

TOSHIBA CMOS DIGITAL INTEGRATED CIRCUIT SILICON MONOLITHIC

**TC74HC367AP, TC74HC367AF, TC74HC367AFN**  
**TC74HC368AP, TC74HC368AF, TC74HC368AFN**

**HEX BUS BUFFER**

**TC74HC367AP/AF/AFN NON - INVERTED (3-STATE)**  
**TC74HC368AP/AF/AFN INVERTED (3-STATE)**

The TC74HC367A and TC74HC368A are high speed CMOS 3 - STATE BUS BUFFERS fabricated with silicon gate C<sup>2</sup>MOS technology.

They achieve the high speed operation similar to equivalent LSTTL while maintaining the CMOS low power dissipation.

They contain six buffers; four buffers are controlled by an enable input ( $\bar{G}1$ ), and the other two buffers are controlled by another enable input ( $\bar{G}2$ ). The outputs of each buffer group are enabled when  $\bar{G}1$  and/or  $\bar{G}2$  inputs are held low; if held high, these outputs are in a high impedance state.

The TC74HC367A is a non - inverting output type, while the TC74HC368A is an inverting output type.

All inputs are equipped with protection circuits against static discharge or transient excess voltage.

**FEATURES :**

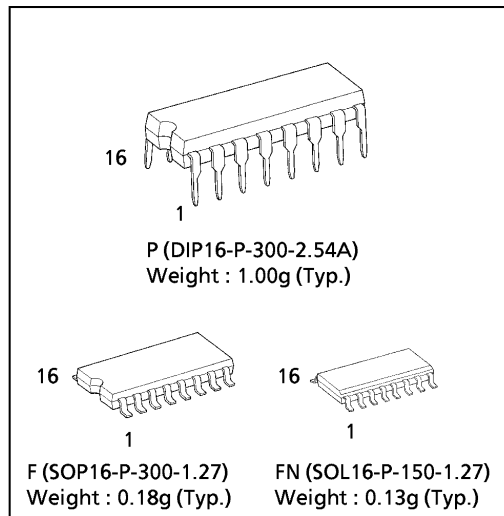
- High Speed..... $t_{pd} = 11\text{ns}(\text{typ.})$  at  $V_{CC} = 5\text{V}$
- Low Power Dissipation..... $I_{CC} = 4\mu\text{A}(\text{Max.})$  at  $T_a = 25^\circ\text{C}$
- High Noise Immunity..... $V_{NIH} = V_{NIL} = 28\% V_{CC} (\text{Min.})$
- Output Drive Capability..... 15 LSTTL Loads
- Symmetrical Output Impedance... $|I_{OH}| = I_{OL} = 6\text{mA}$
- Balanced Propagation Delays..... $t_{pLH} \approx t_{pHL}$
- Wide Operating Voltage Range... $V_{CC} (\text{opr.}) = 2\text{V} \sim 6\text{V}$
- Pin and Function Compatible with 74LS367/368

**TRUTH TABLE**

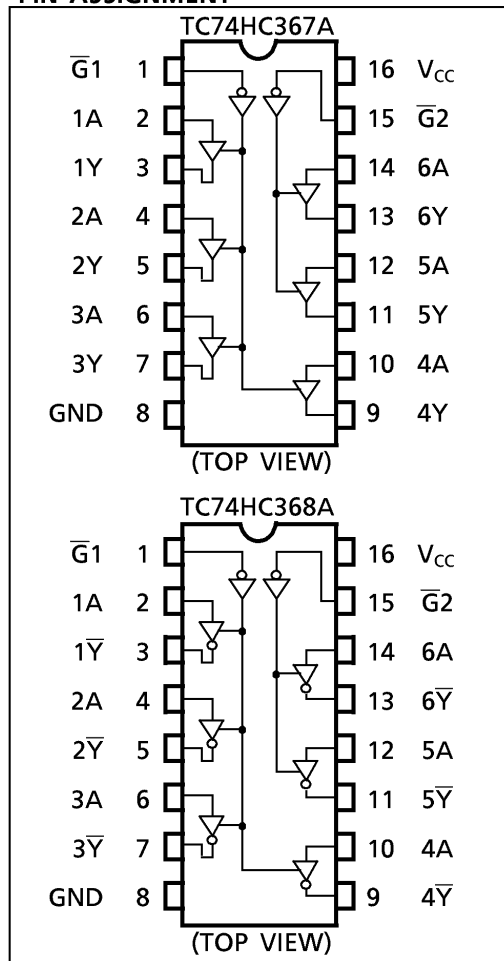
INPUTS		OUTPUTS	
$\bar{G}$	$A_n$	Y(367A)	$\bar{Y}$ (368A)
L	L	L	H
L	H	H	L
H	X	Z	Z

X : Don't Care, Z : High Impedance

(Note) The JEDEC SOP (FN) is not available in Japan.



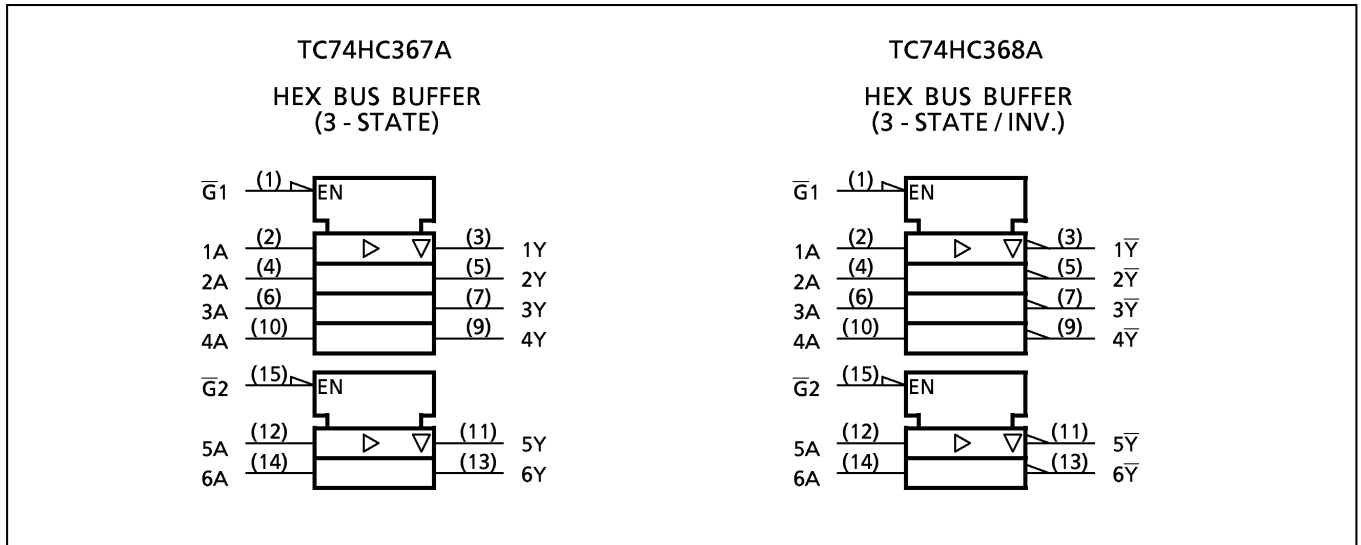
**PIN ASSIGNMENT**



961001EBA2

● TOSHIBA is continually working to improve the quality and the reliability of its products. Nevertheless, semiconductor devices in general can malfunction or fail due to their inherent electrical sensitivity and vulnerability to physical stress. It is the responsibility of the buyer, when utilizing TOSHIBA products, to observe standards of safety, and to avoid situations in which a malfunction or failure of a TOSHIBA product could cause loss of human life, bodily injury or damage to property. In developing your designs, please ensure that TOSHIBA products are used within specified operating ranges as set forth in the most recent products specifications. Also, please keep in mind the precautions and conditions set forth in the TOSHIBA Semiconductor Reliability Handbook.

IEC LOGIC SYMBOL



961001EBA2'

- The products described in this document are subject to foreign exchange and foreign trade control laws.
- The information contained herein is presented only as a guide for the applications of our products. No responsibility is assumed by TOSHIBA CORPORATION for any infringements of intellectual property or other rights of the third parties which may result from its use. No license is granted by implication or otherwise under any intellectual property or other rights of TOSHIBA CORPORATION or others.
- The information contained herein is subject to change without notice.

## ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage Range	$V_{CC}$	-0.5~7	V
DC Input Voltage	$V_{IN}$	-0.5~ $V_{CC}+0.5$	V
DC Output Voltage	$V_{OUT}$	-0.5~ $V_{CC}+0.5$	V
Input Diode Current	$I_{IK}$	±20	mA
Output Diode Current	$I_{OK}$	±20	mA
DC Output Current	$I_{OUT}$	±35	mA
DC $V_{CC}$ /Ground Current	$I_{CC}$	±75	mA
Power Dissipation	$P_D$	500 (DIP)* / 180 (SOP)	mW
Storage Temperature	$T_{stg}$	-65~150	°C

\*500mW in the range of  $T_a = -40^{\circ}\text{C} \sim 65^{\circ}\text{C}$ . From  $T_a = 65^{\circ}\text{C}$  to  $85^{\circ}\text{C}$  a derating factor of  $-10\text{mW}/^{\circ}\text{C}$  shall be applied until 300mW.

## RECOMMENDED OPERATING CONDITIONS

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage	$V_{CC}$	2~6	V
Input Voltage	$V_{IN}$	0~ $V_{CC}$	V
Output Voltage	$V_{OUT}$	0~ $V_{CC}$	V
Operating Temperature	$T_{opr}$	-40~85	°C
Input Rise and Fall Time	$t_r, t_f$	0~1000 ( $V_{CC} = 2.0\text{V}$ ) 0~500 ( $V_{CC} = 4.5\text{V}$ ) 0~400 ( $V_{CC} = 6.0\text{V}$ )	ns

## DC ELECTRICAL CHARACTERISTICS

PARAMETER	SYMBOL	TEST CONDITION	$V_{CC}$ (V)	$T_a = 25^{\circ}\text{C}$			$T_a = -40 \sim 85^{\circ}\text{C}$		UNIT	
				MIN.	TYP.	MAX.	MIN.	MAX.		
High - Level Input Voltage	$V_{IH}$		2.0	1.50	—	—	1.50	—	V	
			4.5	3.15	—	—	3.15	—		
			6.0	4.20	—	—	4.20	—		
Low - Level Input Voltage	$V_{IL}$		2.0	—	—	0.50	—	0.50	V	
			4.5	—	—	1.35	—	1.35		
			6.0	—	—	1.80	—	1.80		
High - Level Output Voltage	$V_{OH}$	$V_{IN} = V_{IH}$ or $V_{IL}$	$I_{OH} = -20\mu\text{A}$	2.0	1.9	2.0	—	1.9	—	V
				4.5	4.4	4.5	—	4.4	—	
				6.0	5.9	6.0	—	5.9	—	
Low - Level Output Voltage	$V_{OL}$	$V_{IN} = V_{IH}$ or $V_{IL}$	$I_{OL} = 20\mu\text{A}$	2.0	—	0.0	0.1	—	0.1	V
				4.5	—	0.0	0.1	—	0.1	
				6.0	—	0.0	0.1	—	0.1	
3 - State Output Off - State Current	$I_{OZ}$	$V_{IN} = V_{IH}$ or $V_{IL}$ $V_{OUT} = V_{CC}$ or GND	6.0	—	—	±0.5	—	±5.0	$\mu\text{A}$	
Input Leakage Current	$I_{IN}$	$V_{IN} = V_{CC}$ or GND	6.0	—	—	±0.1	—	±1.0		
Quiescent Supply Current	$I_{CC}$	$V_{IN} = V_{CC}$ or GND	6.0	—	—	4.0	—	40.0		

AC ELECTRICAL CHARACTERISTICS (Input  $t_r = t_f = 6\text{ns}$ )

PARAMETER	SYMBOL	TEST CONDITION			Ta = 25°C			Ta = -40~85°C		UNIT
			CL	V <sub>CC</sub> (V)	MIN.	TYP.	MAX.	MIN.	MAX.	
Output Transition Time	$t_{TLH}$ $t_{THL}$		50	2.0	—	25	60	—	75	ns
				4.5	—	7	12	—	15	
				6.0	—	6	10	—	13	
Propagation Delay Time	$t_{pLH}$ $t_{pHL}$		50	2.0	—	36	95	—	120	
				4.5	—	12	19	—	24	
				6.0	—	10	16	—	20	
			150	2.0	—	40	130	—	165	
				4.5	—	16	26	—	33	
				6.0	—	14	22	—	28	
Output Enable Time	$t_{pZL}$ $t_{pZH}$	$R_L = 1\text{k}\Omega$	50	2.0	—	36	120	—	150	
				4.5	—	12	24	—	30	
				6.0	—	10	20	—	26	
			150	2.0	—	40	160	—	200	
				4.5	—	16	32	—	40	
				6.0	—	14	27	—	34	
Output Disable Time	$t_{pLZ}$ $t_{pHZ}$	$R_L = 1\text{k}\Omega$	50	2.0	—	35	120	—	150	
				4.5	—	15	24	—	30	
				6.0	—	13	20	—	26	
Input Capacitance	$C_{IN}$				—	5	10	—	pF	
Output Capacitance	$C_{OUT}$				—	10	—	—		
Power Dissipation Capacitance	$C_{PD} (1)$	TC74HC367A			—	36	—	—		—
		TC74HC368A			—	30	—	—		—

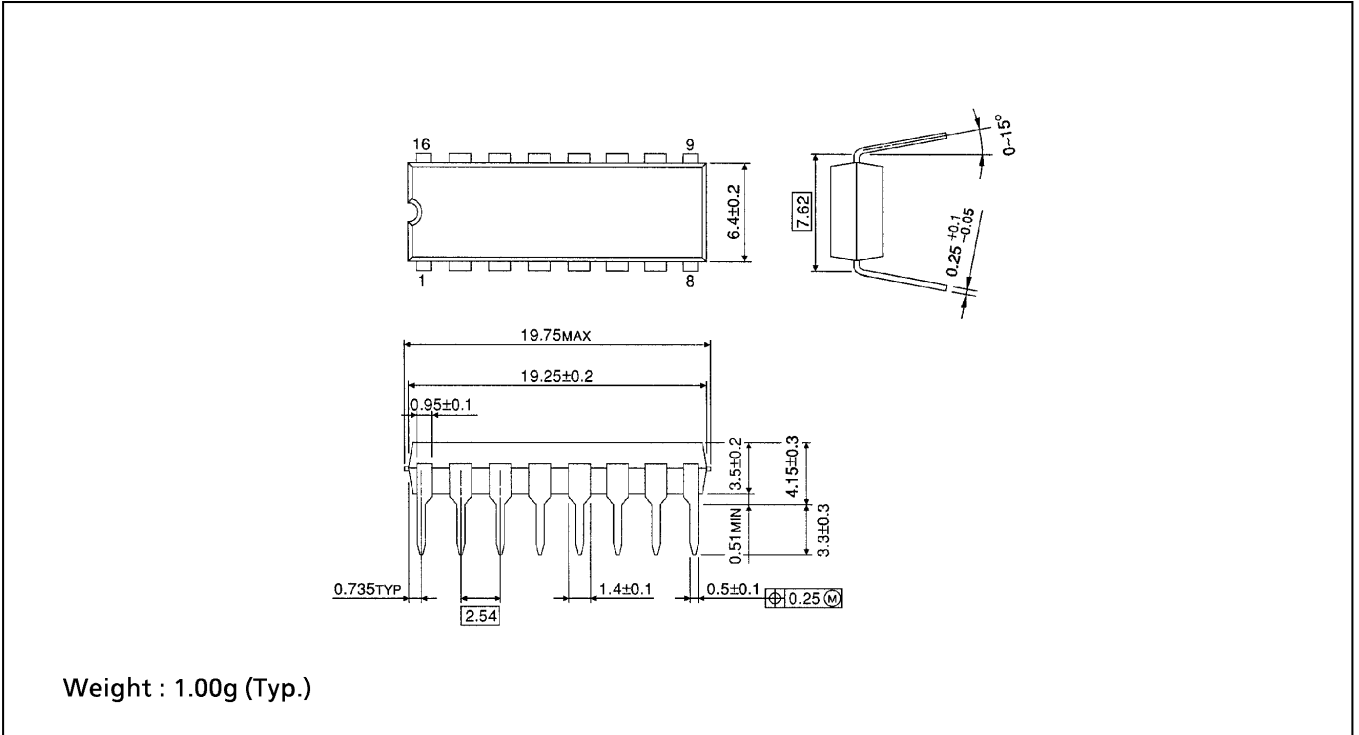
Note (1)  $C_{PD}$  is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation :

$$I_{CC}(\text{opr}) = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/6 \text{ (per bit)}$$

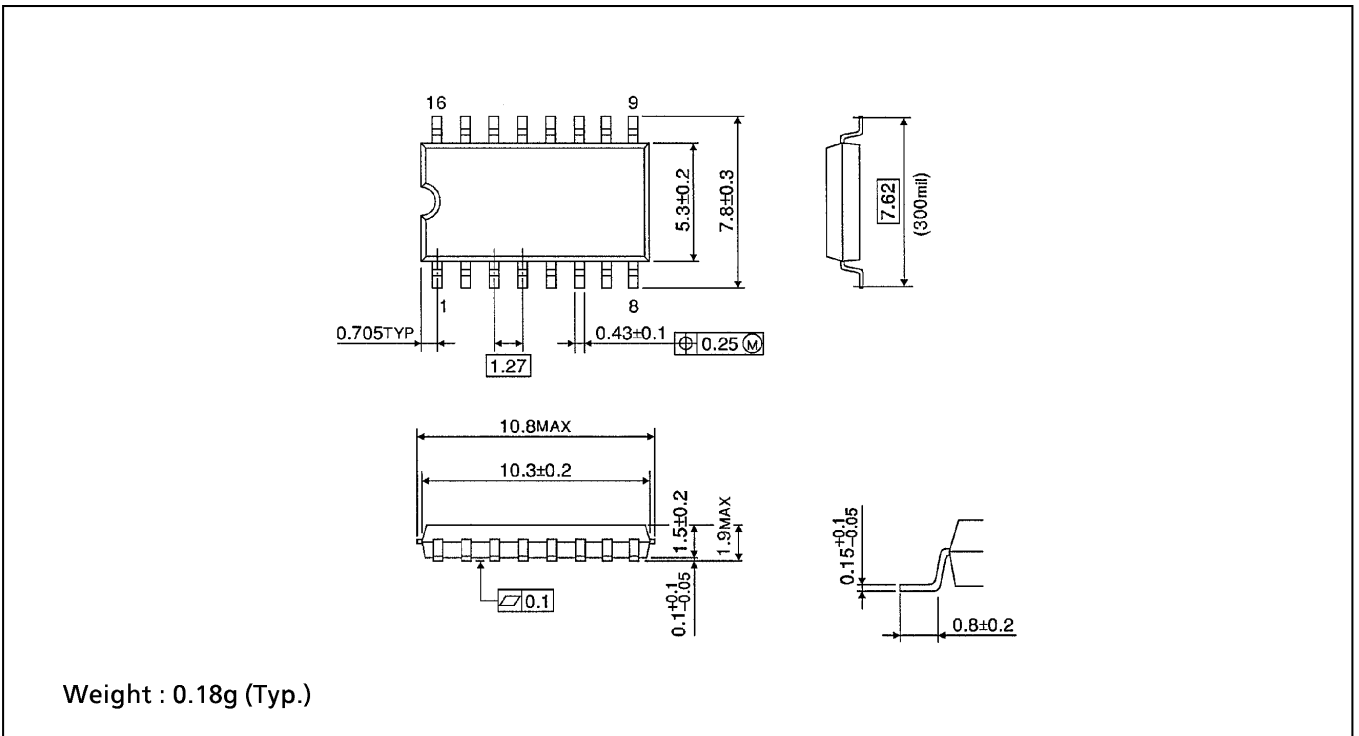
**DIP 16PIN OUTLINE DRAWING (DIP16-P-300-2.54A)**

Unit in mm



**SOP 16PIN (200mil BODY) OUTLINE DRAWING (SOP16-P-300-1.27)**

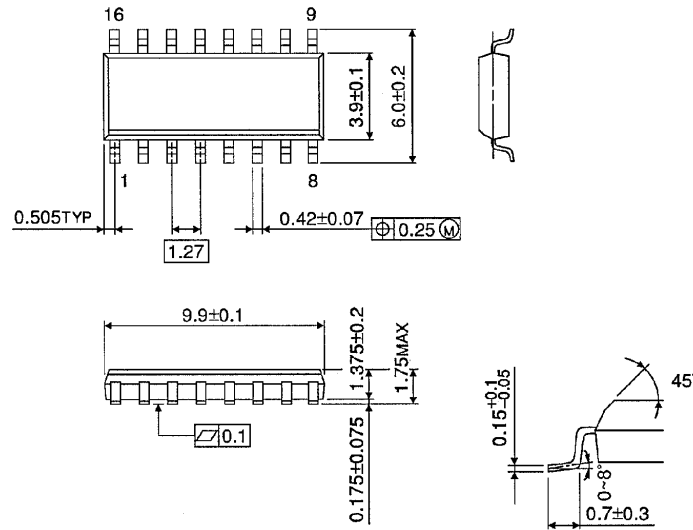
Unit in mm



**SOP 16PIN (150mil BODY) OUTLINE DRAWING (SOL16-P-150 -1.27)**

Unit in mm

(Note) This package is not available in Japan.



Weight : 0.13g (Typ.)